			0312000.2		PCN Date: Mar 18, 2020			4ar 18, 2020		
I ITIQ'	Qualification ABCD05HV d		O8 as an a	ddition	al Fab and Ass	sembly	site	e optio	ns for select	
Customer Contact:			PCN Manag	<u>ler</u>		Dept:			Quality Services	
Proposed 1 st Ship Date:									Date provided at sample request.	
Change Typ	Change Type:									
	Assembly Site			bly Pro	cess			Asse	mbly Materials	
Design			Electri	cal Spe	cification			Mech	anical Specification	
Test Sit				<u>.</u>	ping/Labeling	g Test Process				
	Bump Site				Material				r Bump Process	
🛛 🛛 Wafer F	ab Site			Fab Ma				Wafe	r Fab Process	
					change Details					
Description	n of Change			PCN	Details					
Texas Instru	iments is ple	ased to			alification of it uct Affected" s			is add	itional fabrication	
	Current	Fab Sit	е			Additi	ona	l Fab	Site	
Current F Site	ab Prod	cess	Wafe Diame		Additional Fab Site	P	Proc	ess	Wafer Diameter	
MAINEFA	B ABCD	05HV	200 m		MIHO8	AE	BCD)5HV	200 mm	
-		Form,	Fit, Funct	ion, Q	uality or Reli	ability	/ (p	ositiv	e / negative):	
	product id	entifica	ation resu	lting f	rom this PCN	-				
Changes to						l:			Chip Site City	
Changes to	e Chip		gin (20L)		rom this PCN Site Country C USA	l:			Chip Site City South Portland	
Changes to Current Chip Sit MAINEFA	ce Chip AB	Site Ori CUA	gin (20L)	Chip	Site Country C USA	l: Code (2	21L)		South Portland	
Changes to Current Chip Sit MAINEFA	ce Chip AB Site ce Chip	Site Ori CUA	gin (20L) A gin (20L)	Chip	Site Country C	l: Code (2	21L)			
Changes to Current Chip Sit MAINEFA New Fab S Chip Sit MIHOS Sample proc NSTRUME MADE IN: N 2DC:	ce Chip Chip Ce Chip	Site Ori CUA Site Ori MH8 label (r G4 AL DT /29/04	gin (20L) A gin (20L) 3	Chip Chip	Site Country C USA Site Country C JPN	Code (2 Code (2 Code (2 74LS(00 DT: 39 Y (1T)	21L) 21L) 21L) 07N((1 9599) 75 (21)	SR 0) 03 047M 52348	Chip Site City Ibaraki	
Changes to Current Chip Sit MAINEFA New Fab S Chip Sit MIHOS Sample proc Sample proc INSTRUME MADE IN: N 2DC: MSL '2 /260 MSL '2 /260 MSL '2 /260 MSL '2 /260	ce Chip AB Site ce Chip B duct shipping Luct shipping C/1 YEAR SC/UNLIM 03 (L)T0:1 Fected:	Site Ori CUA Site Ori MHE label (r G4 AL DT /29/04	gin (20L) A gin (20L) 3	Chip Chip	Site Country C USA Site Country C JPN t label) t label) t (1P) SN (Q) 20 (31T) LC (4W) TK (P) (20L) CSO	Code (2 Code (2 Code (2 74LS(00 DT: 39 Y (1T)	21L) 21L) 21L) 07N((1 9599) 75 (21) 211)	SR 0) 03 047M 52348 L) CCC L) ACC	Chip Site City Ibaraki	
Changes to Current Chip Sit MAINEFA New Fab S Chip Sit MIHOS Sample proc Sample proc MSL 1 /235 OPT: ITEM: LBL: 5A Product Aff	ce Chip	Site Ori CUA Site Ori Iabel (r G4 AL DT /29/04 9 750	gin (20L) gin (20L) not actual	Chip Chip product	Site Country C USA Site Country C JPN t label) t label) (1P) SN (Q) 20 (31T) LC (4W) TK (P) (20L) CSO (22L) ASO	Code (2 Code (2 74LS(00 07:39 Y (1T)	21L) 21L) 21L) 07N (1 59 59 575 (21)	SR 0) 03 047M 5234E L) ACC L) ACC LM34	South Portland Chip Site City Ibaraki	

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approve Date 15-January-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as. Number of lots / Total sample size / Total failed								
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: LM34919CQTLX/NOPB	QBS Process Reference TCAN1042HVDRQ1	
Test Grou	Test Group A – Accelerated Environment Stress Tests								
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0	
uHAST	A3	JEDEC JESD22- A102	3	77	Un-biased HAST, 130C/85%RH	96 Hours	3/231/1 (Note 1)	3/231/0	
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0	
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	NA	
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	1/45/0	1/45/0	
Test Grou	р B – А	ccelerated Lifetime Sin	nulation	n Tests	i				
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 125C	1000 Hours	3/231/0	3/231/0	
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0	
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	N/A	
Test Grou	p C – P	ackage Assembly Integ	rity Te	sts					
SD	C3	JEDEC JESD22- B102	1	15	Solderability (>95% Lead Coverage)	Pb & Pb-Free	N/A	N/A	
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	N/A	N/A	
SBS	C5	AEC Q100-010 AEC Q003	3	10	Solder Ball Shear	Solder Ball	N/A	N/A	
Test Grou	pD-D	ie Fabrication Reliabili	ty Test	5					
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	

Test Group E – Electrical Verification Tests									
	HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0
	CDM	E3	AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	1/3/0
	LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/6/0
	ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold Test	3/90/0	3/90/0

Qual Device LM34919CQTLX/NOPB is qualified at LEVEL1-260C

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable. Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

Note 1: One discounted fail attributed to die damage likely caused by handling issues. FA report attached to eQDB.

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

LM25117QPMHX/NOPB Maine to Miho Approve Date 07-January-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as. Number of fotal sample size / fotal failed							
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: LM25117QPMHX/NOPB	QBS Process Reference TCAN1042HVDRQ1
Test Group	A – A	ccelerated Environmer	nt Stres					
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0
AC	A3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	30	Post Temp. Cycle Bond Pull	Wires	1/30/0	1/30/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	NA
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	1/45/0	1/45/0
Test Group	B – A	ccelerated Lifetime Sin	nulatio	n Tests				
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 125C	1000 Hours	3/231/1 (Note 1)	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0
EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	N/A
Test Group	C – P	ackage Assembly Integ	grity Te	sts				
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	1/30/0
SD	СЗ	JEDEC JESD22- B102	1	15	Solderability (>95% Lead Coverage)	Pb & Pb-Free	N/A	N/A
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	N/A	N/A
Test Group	D – D	ie Fabrication Reliabili	ty Test	5				
EM	D1	JESD61	-	-	Electromigration		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Test Group E – Electrical Verification Tests								
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold Test	3/90/0	3/90/0

Qual Device LM25117QPMHX/NOPB is qualified at LEVEL3-260C A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable. Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED Room/Hot/Cold : HTOL, ED Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

Note 1: 1 discounted fail that occurred at 168 hrs has been attributed to EOS most likely caused by handling issues. FA report attached to EQDB.

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com

Texas Instruments Incorporated

WW PCN Team

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (<u>www.ti.com/legal/termsofsale.html</u>) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.